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It has come to our attention after the publication of our letter that Eq. (15) in the letter is an expression obtained by taking the outer shell (region I) of the particle as an equivalent sphere, but it is not the solution of the diffusion Eq. (8). An alternate description can be obtained by considering the gas atom diffusion into a hollow spherical shell. In this case, the $f$-type gas atom concentration distribution in the hollow can be obtained by solving Eq. (8) whose solution is

$$c_f(r,t) = \frac{c_{f0}R(r-R_0) + c_f(R_0)R_0(R-r)}{r(R-R_0)} + \sum_{m=1}^{\infty} \frac{c_{f0}R \cos m \pi - c_f(R_0)R_0}{\sin m \pi} \frac{m \pi (r-R_0)}{(R-R_0)^2} e^{-m^2 \pi^2 D_f/4(R-R_0)^2}.$$  (1)

In the case where $D_f \approx D_t$, the $f$-type atoms actually reach the steady distribution in region I for each $R_0$, i.e.,

$$C_f(r,t) = \frac{c_{f0}R(r-R_0) + c_f(R_0)R_0(R-r)}{r(R-R_0)}.$$  (2)

For the nitrogenation of $R_2Fe_{17}$ systems, since $c_{f0} \ll c_{t0}$, the possible difference between the $f$-type N atom distribution profiles in the nitrided region is experimentally unobservable. Therefore, whether using Eq. (15) given in our letter or using Eq. (1) cited here will not affect the result. However, in dealing with other trapping diffusion problems, Eq. (1) may be a more reasonable description.

1 R. M. Barrer, Philos. Mag. 35, 802 (1944).

Erratum: “Optical investigation of quaternary GaInAsSb/AlGaAsSb strained multiple quantum wells” [Appl. Phys. Lett. 67, 3432 (1995)]

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An error appears in the list of addresses. It should read as follows:

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